SENSITRON
 SEMICONDUCTOR

TECHNICAL DATA
DATA SHEET 6119, REV -

SMALL SIGNAL / COMPUTER DIODE CHIP

FEATURES / BENEFITS:

✓ Die fabricated on a MIL-PRF-19500 JANKCD/JANHCD qualified manufacturing line

✓ Class H and class K element evaluation per MIL-PRF-19500/169

✓ All ratings are @ T_A = 25 °C unless otherwise specified

ELECTRICAL CHARACTERISTICS:

**MAXIMUM RATINGS**   ALL RATINGS ARE AT T_A = 25 °C UNLESS OTHERWISE SPECIFIED

RATING		SYMBOL	MAX.	UNITS
BREAKDOWN VOLTAGE	(I_R = 100 µA)	V_{BR}	200	Volts
WORKING PEAK REVERSE VOLTAGE		V_{RWM}	175	Volts
AVERAGE RECTIFIED FORWARD CURRENT	(T_A=75ºC)	I_o	100	mA
PEAK SINGLE CYCLE SURGE CURRENT (PEAK)	(t_p = 1.0s)	I_{FSM}	500	mA
	(t_p = 1.0µs)		2.0	A
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE		$T_{op, stg}$	-65 to +175	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC		SYMBOL	MAX.	UNITS
MAXIMUM FORWARD VOLTAGE DROP	(I_F = 100 mA dc)	V_{F1}	1.0	Volt
	(T_A=-55ºC, I_F = 100 mA dc)	V_{F2}	1.2	Volt
REVERSE CURRENT	(V_R = V_{RWM})	I_{R1}	0.1	µA dc
	(T_A=+150ºC, V_R = V_{RWM})	I_{R2}	100	µA dc
CAPACITANCE	(V_R = 0 Vdc; V_{sig}=50 mV$_{(p-p)}$ max, f = 1 MHz)	C_{T1}	5.0	pF
MAXIMUM REVERSE RECOVERY TIME	(I_F = I_R = 30 mA, I_{RR} = 3mA)	t_{rr}	50	ns

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PACKAGE DIMENSIONS (inches/mm):
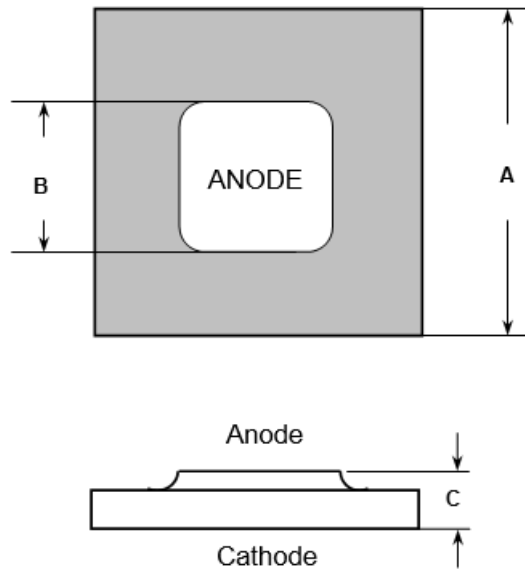
Ltr	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
A	.016	.020	0.406	0.508
B	.008	.010	0.203	0.254
C	.008	.012	0.203	0.305

NOTES: 1. Dimensions are in inches.
2. Millimeter equivalents are given for general information only.
3. The die thickness is .010 (0.25 mm) ±.002 inches (±0.05 mm).
Anode metallization: Al, thickness = 45,000 Å nominal;
Cathode metallization: Ti/Ni/Au (1,200 Å / 1,800 Å / 4,000 Å) nominal.

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PART ORDERING INFORMATION:

J A N x C D 1 N X X X X

Quality level   **Industry part number**

Quality Level:

Suffix	Part Number	Description
H	*JANHCD1N3070*	*Class H level*
K	*JANKCD1N3070*	*Class K level*